

	Type	L #	Hits	Search Text	DBs	Time Stamp
5	BRS	L5	0	3 and memory adj cell	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/1 5 13:58
6	BRS	L6	653	349/38	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/1 5 13:50
7	BRS	L7	5	6 and memory adj cell	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/1 5 13:51
8	BRS	L8	3	6 and frame adj memory	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/1 5 13:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
9	BRS	L9	0	1 and memory	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB	2003/04/1 5 15:14
10	BRS	L10	8087	liquid adj crystal and gate adj insulat\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB	2003/04/1 5 15:17
11	BRS	L11	172	10 and ((two?layer laminat\$3) near gate)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB	2003/04/1 5 15:33
12	BRS	L12	64	11 and storage	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB	2003/04/1 5 15:33

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L14	18	13 and storage	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/15 15:33
14	BRS	L13	42	10 and (two?layer near gate)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/15 15:43
15	BRS	L15	4	10 and (two?layer near gate adj electrode)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/15 15:53
16	BRS	L16	3	5998838.pn.	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/04/15 16:14